	Application No.	Applicant(s)	
AL C. LEAD. LEWIS	10/647,242	7/647,242 TAKEHIRO HASEGWAA	
Notice of Allowability	Examiner	Art Unit	
	Son L. Mai	2827	
The MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT F of the Office or upon petition by the applicant. See 37 CFR 1.31	S (OR REMAINS) CLOSED in i) or other appropriate commu RIGHTS. This application is s	this application. If not inclunication will be mailed in du	ided ie course. THIS
1. This communication is responsive to papers filed 8-26-03	and 1-23-04.		•
2. ☑ The allowed claim(s) is/are <u>1-30</u> .			
3. $igotimes$ The drawings filed on <u>26 August 2003</u> are accepted by th	e Examiner.		
4. Acknowledgment is made of a claim for foreign priority to a) All b) □ Some* c) □ None of the: 1. △ Certified copies of the priority documents have 2. □ Certified copies of the priority documents have 3. □ Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). * Certified copies not received: □ Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONI THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. □ A SUBSTITUTE OATH OR DECLARATION must be submin INFORMAL PATENT APPLICATION (PTO-152) which give the Corrected DRAWINGS (as "replacement sheets") must be comply including changes required by the Notice of Draftspering to Paper No./Mail Date □ Corrected Data (b) □ including changes required by the attached Examine Paper No./Mail Date □ Corrected Data (b) □ including changes required by the attached Examined Paper No./Mail Date □ Corrected Data (b) □ including changes required by the attached Examined Paper No./Mail Date □ Corrected Data (b) □ including changes required by the attached Examined Data (c) □ Corrected Data (d) □ Including Changes required by the attached Examined Data (d) □ Including Changes required by the attached Examined Data (d) □ Including Changes required Data (d) □ Including Changes (d) □ Including	re been received. re been received in Application occuments have been received. " of this communication to file MENT of this application. mitted. Note the attached EXA was reason(s) why the oath or just be submitted. rson's Patent Drawing Reviewals. "'s Amendment / Comment or	n No If in this national stage application a reply complying with the remarkable of the stage application is deficient. If in the Office action of	requirements NOTICE OF
Identifying indicia such as the application number (see 37 CFR each sheet. Replacement sheet(s) should be labeled as such in 7. DEPOSIT OF and/or INFORMATION about the deposition of the second sheet in th	the header according to 37 CF	R 1.121(d).	
attached Examiner's comment regarding REQUIREMENT			
Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☑ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB	6. ☐ Interview St Paper No./I	formal Patent Application (P ummary (PTO-413), Mail Date Amendment/Comment	TO-152)
Paper No./Mail Date 8-26-03;1-23-04 4. Examiner's Comment Regarding Requirement for Deposit of Biological Material		Statement of Reasons for A	

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DETAILED ACTION

1. The papers filed 08-26-03 and 01-23-04 have been entered. Claims 1-30 are pending in the application.

Priority

2. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

Information Disclosure Statement

3. The information disclosure statements filed 08-26-03 and 01-23-04 have been considered.

Allowable Subject Matter

- 4. Claims 1-30 are allowed.
- 5. The following is an examiner's statement of reasons for allowance: The prior art of record fails to teach or suggest a semiconductor memory device comprising: memory cells each of which includes a floating gate MOS transistor and a select MOS transistor in series with the floating gate MOS transistor, select gate lines each of which is formed by connecting commonly the gates of the select MOS transistors of the memory cells in the same row, and first metal wiring layers which are provided for every select gate lines, each of which is formed in the row direction so as to pass through almost the central part of the memory cells, is connected electrically to the corresponding one of the select gate lines, and transmits a row select signal for the second row decoder to select the select gate line.

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6. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

7. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. The references cited in form PTO-892 disclose memory cells in semiconductor memory devices wherein each memory cell comprises a floating gate transistor connected in series with a select transistor.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Son L. Mai whose telephone number is 571-272-1786.

The examiner can normally be reached on 8am to 6pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Hoai Ho can be reached on 571-272-1777. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

04-22-05

SON L. MAI PRIMARY EXAMINER